High voltage fast-switching NPN power transistor

Features

- Low spread of dynamic parameters
- Minimum lot-to-lot spread for reliable operation
- Very high switching speed

Applications

- Electronic ballast for fluorescent lighting
- Switch mode power supplies

Description

These devices are high voltage fast-switching NPN power transistors, manufactured using high voltage multi-epitaxial planar technology for high switching speeds.

They employ a cellular emitter structure with planar edge termination to enhance switching speeds, while maintaining a wide RBSOA.

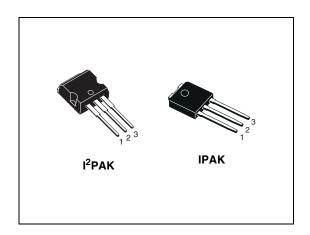


Figure 1. Internal schematic diagram

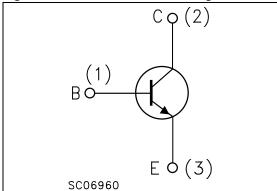


Table 1. Device summary

Order codes	Marking	Package	Packaging
STI13005-H	l13005	I ² PAK	Tube
STU13005	U13005	IPAK	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Complete	Baramatar	Value		11	
Symbol	Parameter	I ² PAK	IPAK	Unit	
V _{CES}	Collector-emitter voltage (V _{BE} = 0)	700		V	
V _{CEO}	Collector-emitter voltage (I _B = 0)	40	00	V	
V _{EBO}	Emitter-base voltage (I _C = 0) 9		V		
I _C	Collector current 4		Α		
I _{CM}	Collector peak current (t _P < 5 ms) 8		Α		
I _B	Base current 2		Α		
I _{BM}	Base peak current (t _P < 5 ms) 4		Α		
P _{TOT}	Total dissipation at $T_c \le 25$ °C	75	30	W	
T _{STG}	Storage temperature	- 65 to 150	- 65 to 150	°C	
TJ	Max. operating junction temperature	150	150	°C	

Table 3. Thermal data

Symbol	Parameter	Va	Unit		
Syllibol	rai ametei	I ² PAK	IPAK	Oille	
R _{thj-case}	Thermal resistance junction-case max	1.7	4.2	°C/W	
R _{thj-amb}	Thermal resistance junction-amb max	62.5	100	°C/W	

2 Electrical characteristics

 T_{case} = 25 °C unless otherwise specified.

Table 4. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{CES}	Collector cut-off current (V _{BE} = 0)	V _{CE} = 700 V V _{CE} = 700 V T _C =125 °C			1 5	mA mA
I _{EBO}	Emitter cut-off current (I _C = 0)	V _{EB} = 9 V			1	mA
V _{CEO(sus)} (1)	Collector-emitter sustaining voltage (I _B = 0)	I _C =10 mA	400			V
V _{CE(sat)} (1)	Collector-emitter saturation voltage	$\begin{split} I_C &= 1 \text{ A} & I_B = 0.2 \text{ A} \\ I_C &= 2 \text{ A} & I_B = 0.5 \text{ A} \\ I_C &= 4 \text{ A} & I_B = 1 \text{ A} \end{split}$			0.5 0.6 1	V V V
V _{BE(sat)} (1)	Base-emitter saturation voltage	$I_C = 1 A$ $I_B = 0.2 A$ $I_C = 2 A$ $I_B = 0.5 A$			1.2 1.6	>
h _{FE} ⁽¹⁾	DC current gain	$I_C = 1 A$ $V_{CE} = 5 V$ $I_C = 2 A$ $V_{CE} = 5 V$	16 8		32 40	
t _s	Resistive load Storage time Fall time	$I_C = 2 \text{ A}$ $V_{CC} = 125 \text{ A}$ $I_{B1} = -I_{B2} = 0.4 \text{ A}$ $I_{D} = 30 \mu\text{s}$		2.2 0.2		µs µs

^{1.} Pulse test: pulse duration = 300 $\mu s,$ duty cycle \leq 2 %.

2.1 Test circuits

Figure 2. Inductive load switching test circuit

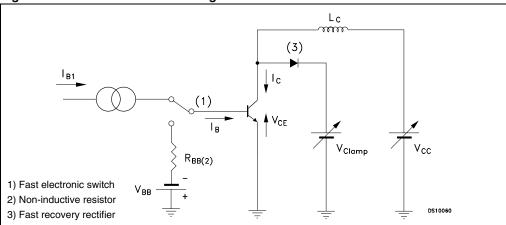
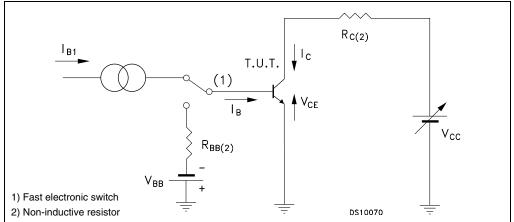


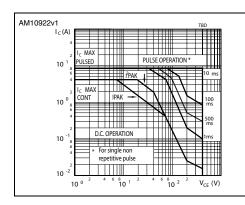
Figure 3. Resistive lad switching test circuit



2.2 Electrical characteristics (curves)

Figure 4. Safe operating area

Figure 5. Derating curve



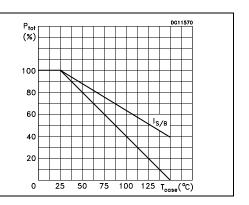
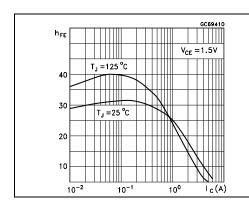


Figure 6. DC current gain ($V_{CE} = 1.5 \text{ V}$) Figure 7. DC current gain ($V_{CE} = 5 \text{ V}$)



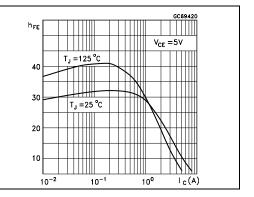
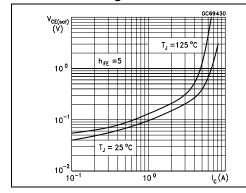
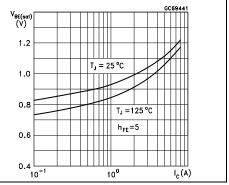


Figure 8. Collector-emitter saturation voltage

Figure 9. Base-emitter saturation voltage

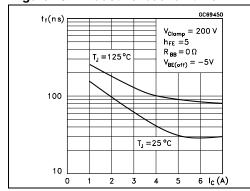




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Figure 10. Inductive load fall time

Figure 11. Inductive load storage time



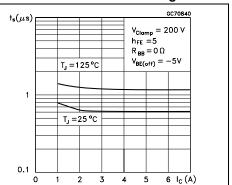
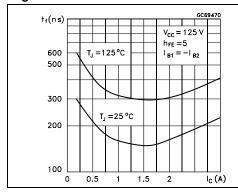


Figure 12. Resistive load fall time

Figure 13. Resistive load storage time



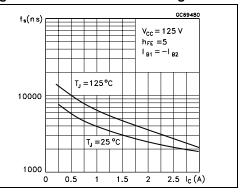
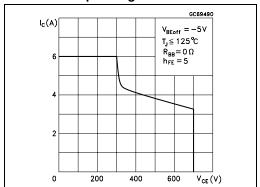


Figure 14. Reverse biased safe operating area



3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of $\mathsf{ECOPACK}^{\mathbb{B}}$ packages, depending on their level of environmental compliance. $\mathsf{ECOPACK}^{\mathbb{B}}$ specifications, grade definitions and product status are available at: $\mathit{www.st.com}$. $\mathsf{ECOPACK}^{\mathbb{B}}$ is an ST trademark.

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Table 5. I²PAK (TO-262) mechanical data

DIM.		mm.	
Dilvi.	min.	typ	max.
Α	4.40		4.60
A1	2.40		2.72
b	0.61		0.88
b1	1.14		1.70
С	0.49		0.70
c2	1.23		1.32
D	8.95		9.35
е	2.40		2.70
e1	4.95		5.15
E	10		10.40
L	13		14
L1	3.50		3.93
L2	1.27		1.40

Figure 15. I²PAK (TO-262) drawing

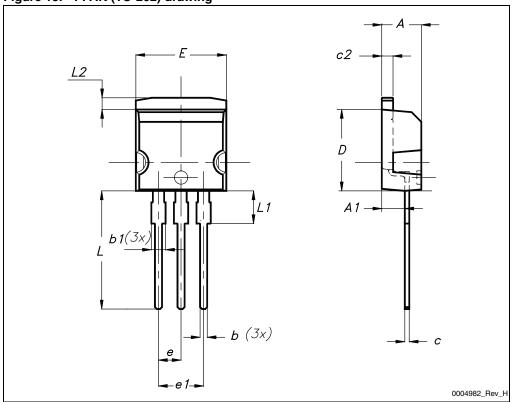


Table 6. IPAK (TO-251) mechanical data

DIM.		mm.	
DIW.	min.	typ	max.
А	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
B5		0.3	
С	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
Е	6.40		6.60
е		2.28	
e1	4.40		4.60
Н		16.10	
L	9.00		9.40
L1	0.80		1.20
L2		0.80	1.00
V1		10 °	

0068771_H

AM09214V1

STI13005-H, STU13005 Revision history

4 Revision history

Table 7. Document revision history

Date	Revision	Changes
13-Dec-2011	1	First release

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